





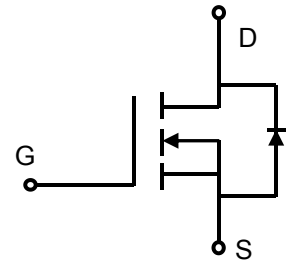



Lonten N-channel 800V, 5A, 0.98Ω LonFET™ Power MOSFET

<p>Description LonFET™ Power MOSFET is fabricated using advanced super junction technology. The resulting device has extremely low on resistance, making it especially suitable for applications which require superior power density and outstanding efficiency.</p> <p>Features</p> <ul style="list-style-type: none"> ◆ Ultra low $R_{DS(on)}$ ◆ Ultra low gate charge (typ. $Q_g = 14.5\text{nC}$) ◆ 100% UIS tested ◆ RoHS compliant <p>Applications</p> <ul style="list-style-type: none"> ◆ Power factor correction (PFC). ◆ Switched mode power supplies (SMPS). ◆ Uninterruptible power supply (UPS). 	<p>Product Summary</p> <table style="width: 100%; border: none;"> <tr> <td style="border: none;">$V_{DS} @ T_{j,max}$</td> <td style="border: none; text-align: right;">850V</td> </tr> <tr> <td style="border: none;">$R_{DS(on),max}$</td> <td style="border: none; text-align: right;">0.98Ω</td> </tr> <tr> <td style="border: none;">I_{DM}</td> <td style="border: none; text-align: right;">5A</td> </tr> <tr> <td style="border: none;">$Q_{g,typ}$</td> <td style="border: none; text-align: right;">14.5nC</td> </tr> </table> <div style="display: flex; justify-content: space-around; align-items: center; margin-top: 10px;"> <div style="text-align: center;">  TO-220 </div> <div style="text-align: center;">  TO-220MF </div> <div style="text-align: center;">  TO-263 </div> <div style="text-align: center;">  TO-262 </div> </div> <div style="display: flex; justify-content: space-around; align-items: center; margin-top: 10px;"> <div style="text-align: center;">  TO-252 </div> <div style="text-align: center;">  TO-251 </div> </div> <div style="text-align: right; margin-top: 20px;">  </div> <div style="text-align: right; margin-top: 10px;">  </div> <p style="text-align: center; margin-top: 10px;">N-Channel MOSFET</p>	$V_{DS} @ T_{j,max}$	850V	$R_{DS(on),max}$	0.98Ω	I_{DM}	5A	$Q_{g,typ}$	14.5nC
$V_{DS} @ T_{j,max}$	850V								
$R_{DS(on),max}$	0.98Ω								
I_{DM}	5A								
$Q_{g,typ}$	14.5nC								

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	800	V
Continuous drain current ($T_C = 25^\circ\text{C}$) ($T_C = 100^\circ\text{C}$)	I_D	5	A
		3	A
Pulsed drain current ¹⁾	I_{DM}	15	A
Gate-Source voltage	V_{GSS}	± 30	V
Avalanche energy, single pulse ²⁾	E_{AS}	120	mJ
Avalanche current, repetitive ³⁾	I_{AR}	5	A
Power Dissipation TO-220MF ($T_C = 25^\circ\text{C}$) - Derate above 25°C	P_D	29	W
		0.23	W/ $^\circ\text{C}$
Power Dissipation TO-220/TO-252/TO-263 ($T_C = 25^\circ\text{C}$) - Derate above 25°C	P_D	50	W
		0.4	W/ $^\circ\text{C}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Continuous diode forward current	I_S	5	A
Diode pulse current	$I_{S,pulse}$	15	A

Thermal Characteristics TO-220/TO-252/TO-263

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62	$^{\circ}\text{C}/\text{W}$
Soldering temperature, wavesoldering only allowed at leads. (1.6mm from case for 10s)	T_{sold}	260	$^{\circ}\text{C}$

Thermal Characteristics TO-220MF

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	4.3	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	80	$^{\circ}\text{C}/\text{W}$
Soldering temperature, wavesoldering only allowed at leads. (1.6mm from case for 10s)	T_{sold}	260	$^{\circ}\text{C}$

Package Marking and Ordering Information

Device	Device Package	Marking	Units/Tube	Units/Real
LSC80R980GT	TO-220	LSC80R980GT	50	
LSD80R980GT	TO-220MF	LSD80R980GT	50	
LSE80R980GT	TO-263	LSE80R980GT		800
LSF80R980GT	TO-262	LSF80R980GT	50	
LSG80R980GT	TO-252	LSG80R980GT		2500
LSH80R980GT	TO-251	LSH80R980GT	72	

Electrical Characteristics $T_c = 25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{\text{GS}}=0\text{ V}, I_{\text{D}}=0.25\text{ mA}$	800	-	-	V
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=0.25\text{ mA}$	2.5	3.5	4.5	V
Drain cut-off current	I_{DSS}	$V_{\text{DS}}=800\text{ V}, V_{\text{GS}}=0\text{ V},$ $T_j = 25^{\circ}\text{C}$ $T_j = 125^{\circ}\text{C}$	-	-	1	μA
Gate leakage current, Forward	I_{GSSF}	$V_{\text{GS}}=30\text{ V}, V_{\text{DS}}=0\text{ V}$	-	-	100	nA
Gate leakage current, Reverse	I_{GSSR}	$V_{\text{GS}}=-30\text{ V}, V_{\text{DS}}=0\text{ V}$	-	-	-100	nA
Drain-source on-state resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}}=10\text{ V}, I_{\text{D}}=2.5\text{ A}$ $T_j = 25^{\circ}\text{C}$ $T_j = 150^{\circ}\text{C}$	-	0.85	0.98	Ω
Gate resistance	R_{G}	$f=1\text{ MHz}, \text{open drain}$	-	7.5	-	Ω
Dynamic characteristics						
Input capacitance	C_{iss}	$V_{\text{DS}} = 100\text{ V}, V_{\text{GS}} = 0\text{ V},$ $f = 250\text{ kHz}$	-	614	-	μF
Output capacitance	C_{oss}		-	20	-	
Reverse transfer capacitance	C_{rss}		-	2	-	

Turn-on delay time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 2.5A$ $R_G = 10\Omega, V_{GS}=10V$	-	13.5	-	ns
Rise time	t_r		-	30	-	
Turn-off delay time	$t_{d(off)}$		-	56	-	
Fall time	t_f		-	27	-	
Gate charge characteristics						
Gate to source charge	Q_{gs}	$V_{DD}=640V, I_D=2.5A,$ $V_{GS}=0 \text{ to } 10V$	-	3.5	-	nC
Gate to drain charge	Q_{gd}		-	5.5	-	
Gate charge total	Q_g		-	14.5	-	
Gate plateau voltage	$V_{plateau}$		-	5	-	V
Reverse diode characteristics						
Diode forward voltage	V_{SD}	$V_{GS}=0V, I_F=2.5A$	-	-	1.4	V
Reverse recovery time	t_{rr}	$V_R=50V, I_F=2.5A,$ $di_F/dt=100A/\mu s$	-	250	-	ns
Reverse recovery charge	Q_{rr}		-	1.69	-	μC
Peak reverse recovery current	I_{rm}		-	13.5	-	A

Notes:

1. Limited by maximum junction temperature, maximum duty cycle is 0.75.
2. $I_{AS} = 2A, V_{DD} = 60V, \text{Starting } T_j = 25^\circ C.$
3. Repetitive Rating: Pulse width limited by maximum junction temperature.

Electrical Characteristics Diagrams

Figure 1. On-Region Characteristics

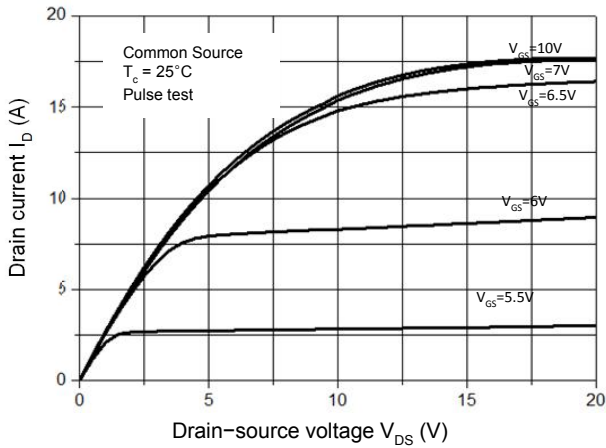


Figure 2. Transfer Characteristics

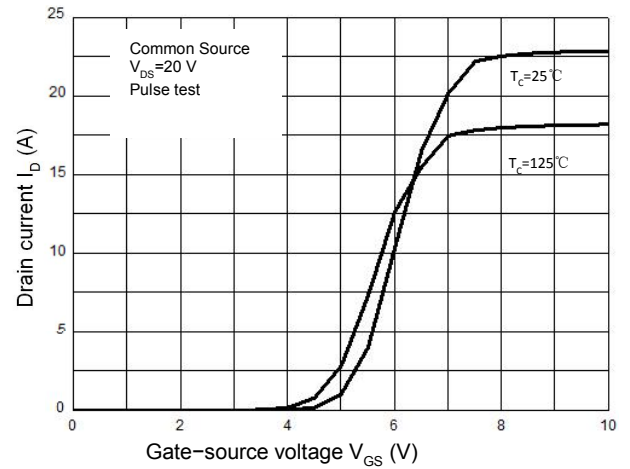


Figure 3. On-Resistance Variation vs. Drain Current

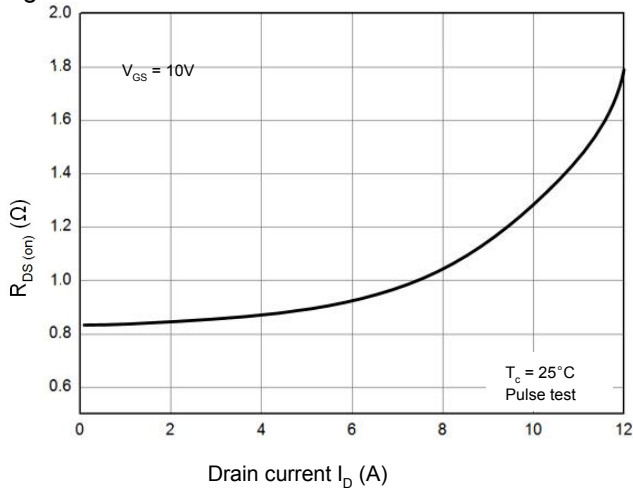


Figure 4. Threshold Voltage vs. Temperature

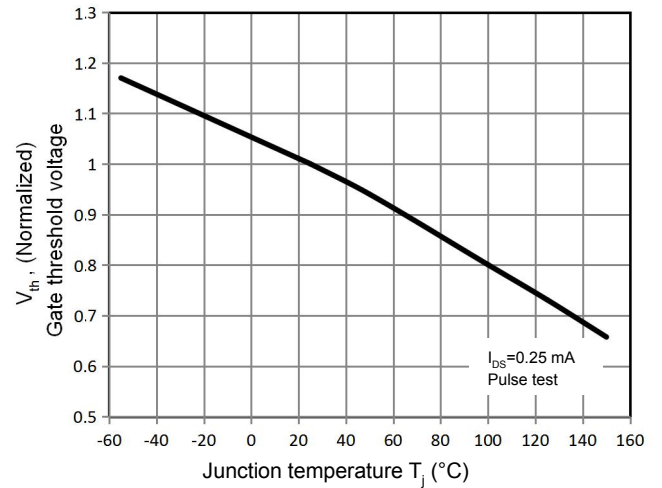


Figure 5. Breakdown Voltage vs. Temperature

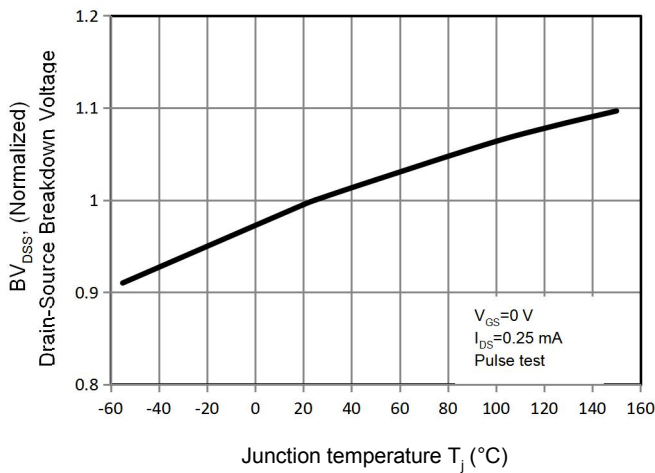


Figure 6. On-Resistance vs. Temperature

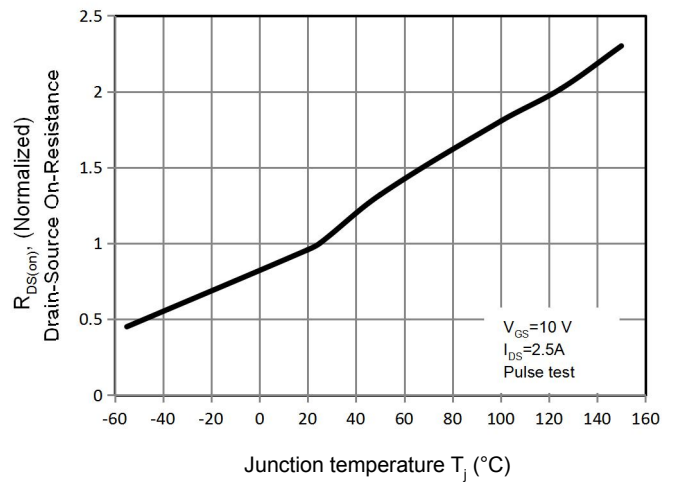


Figure 7. Capacitance Characteristics

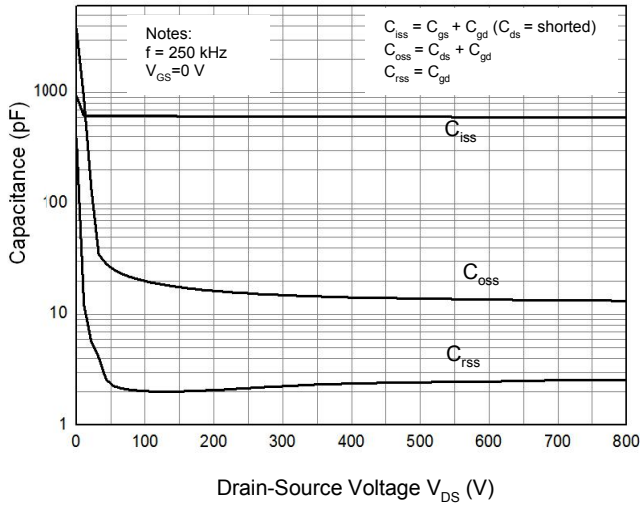


Figure 8. Gate Charge Characterist

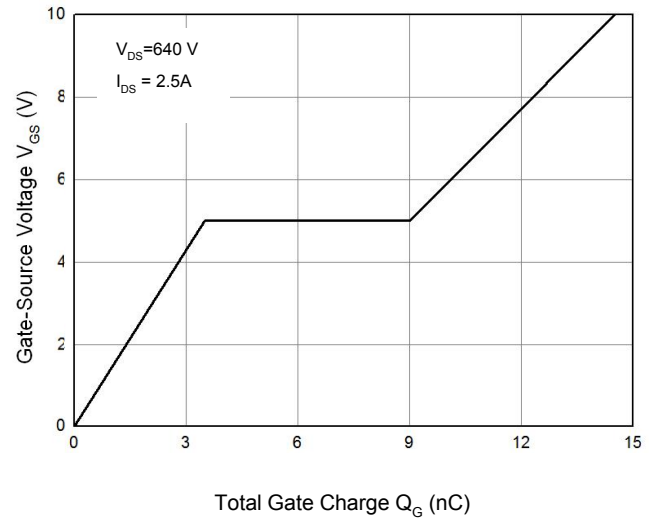


Figure 9.1 Maximum Safe Operating Area
TO-220MF

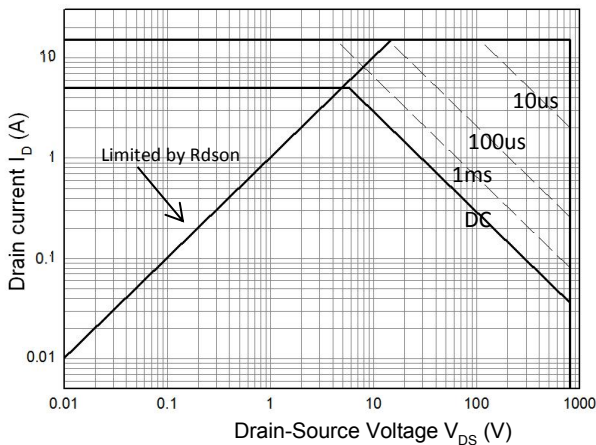


Figure 9.2 Maximum Safe Operating Area
TO-220/TO-252/TO-263

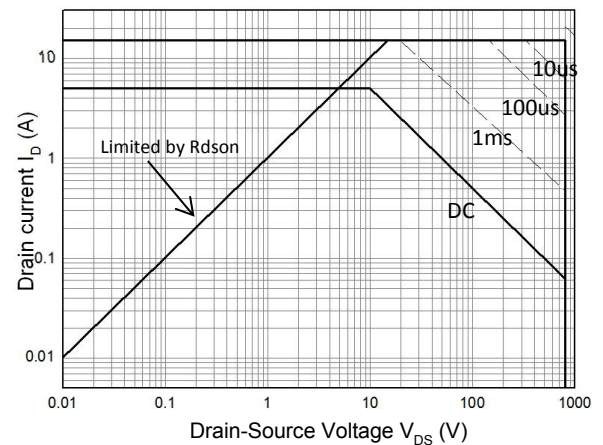


Figure 10.1 Power Dissipation vs. Temperature
TO-220MF

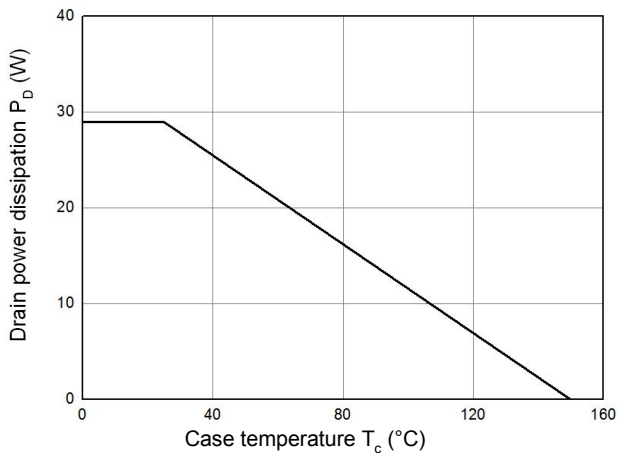
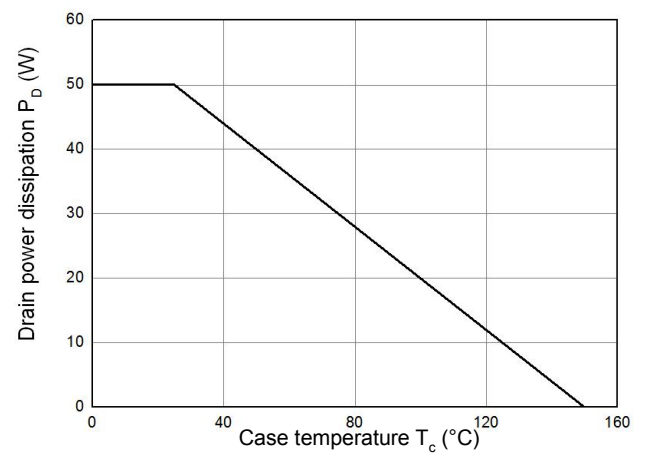
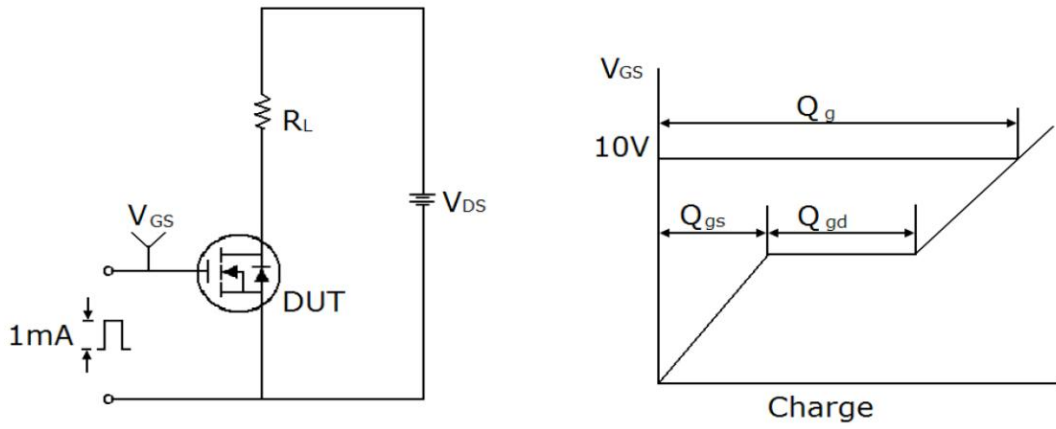


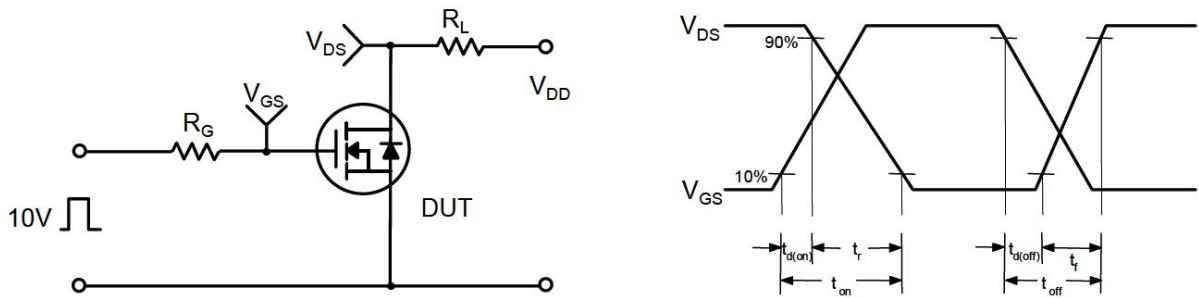
Figure 10.2 Power Dissipation vs. Temperature
TO-220/TO-252/TO-263



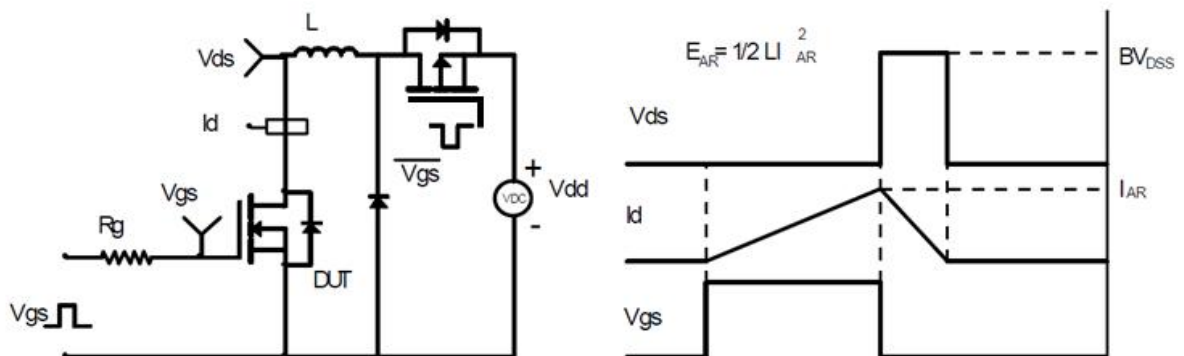
Gate Charge Test Circuit & Waveform



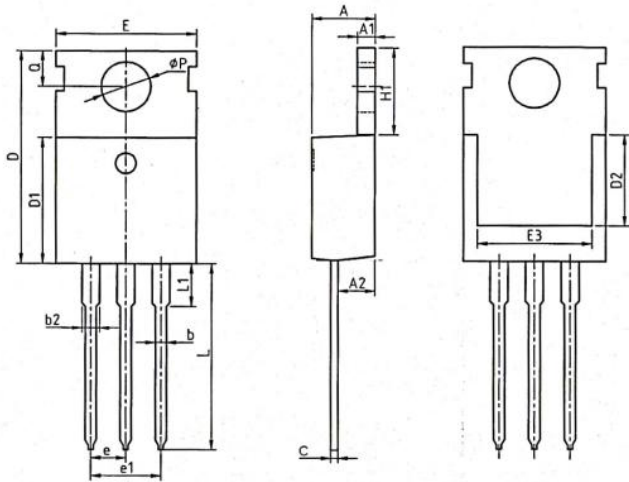
Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

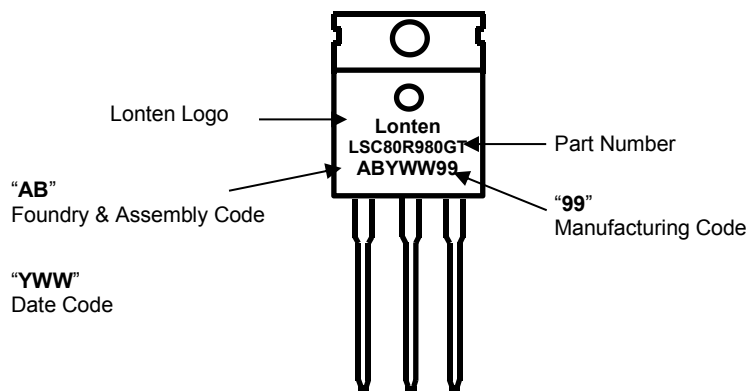


Mechanical Dimensions for TO-220

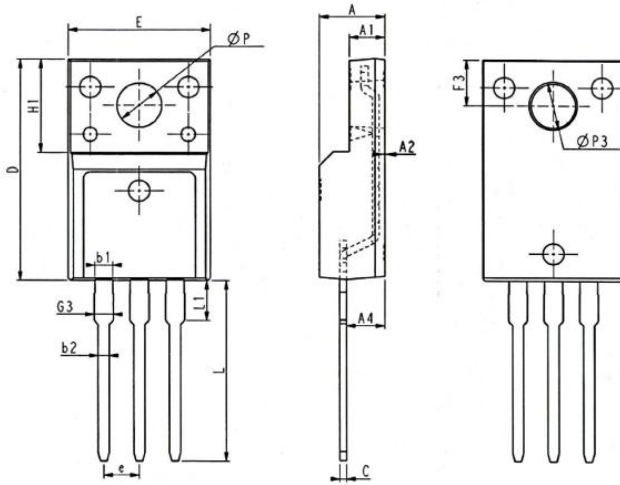


COMMON DIMENSIONS						
SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.37	4.57	4.70	0.172	0.180	0.185
A1	1.25	1.30	1.40	0.049	0.051	0.055
A2	2.20	2.40	2.60	0.087	0.094	0.102
b	0.70	0.80	0.95	0.028	0.031	0.037
b2	1.17	1.27	1.47	0.046	0.050	0.058
c	0.45	0.50	0.60	0.018	0.020	0.024
D	15.10	15.60	16.10	0.594	0.614	0.634
D1	8.80	9.10	9.40	0.346	0.358	0.370
D2	5.50	—	—	0.217	—	—
E	9.70	10.00	10.30	0.382	0.394	0.406
E3	7.00	—	—	0.276	—	—
e	2.54BSC			0.1BSC		
e1	5.08BSC			0.2BSC		
H1	6.25	6.50	6.85	0.246	0.256	0.270
L	12.75	13.50	13.80	0.502	0.531	0.543
L1	—	3.10	3.40	—	0.122	0.134
Øp	3.40	3.60	3.80	0.134	0.142	0.150
Q	2.60	2.80	3.00	0.102	0.110	0.118

TO-220 Part Marking Information

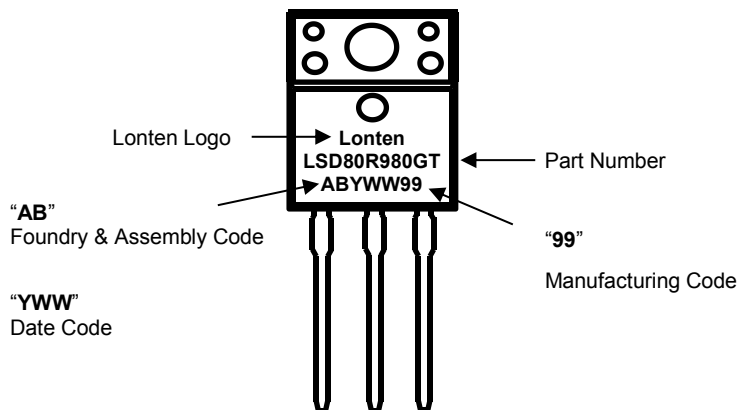


Mechanical Dimensions for TO-220MF

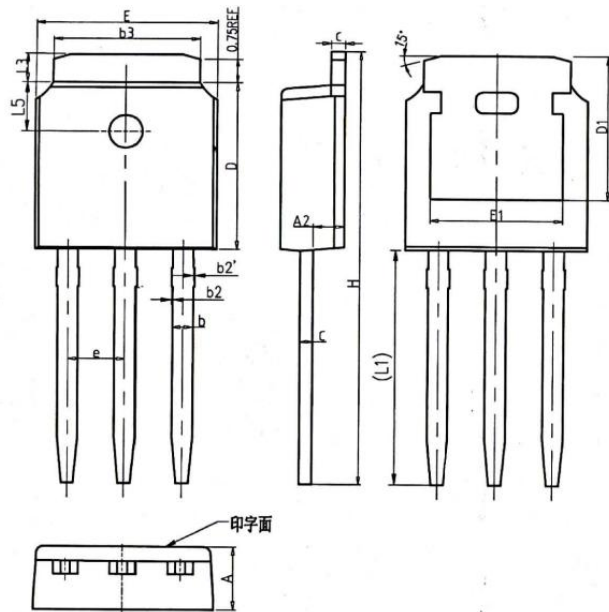


SYMBOL	COMMON DIMENSIONS					
	MM			INCH		
	MIN	NOM	MAX	MIN	NO	MA
E	9.96	10.1	10.3	0.39	0.40	0.40
A	4.50	4.70	4.90	0.17	0.18	0.19
A1	2.34	2.54	2.74	0.09	0.10	0.10
A2	0.30	0.45	0.60	0.01	0.00	0.02
A4	2.65	2.76	2.96	0.10	0.10	0.11
C	0.40	0.50	0.38	0.01	0.02	0.02
D	15.57	15.8	16.1	0.61	0.62	0.63
H1	6.70REF			0.264REF		
e	2.54BSC			0.1BSC		
ØP	3.03	3.18	3.38	0.11	0.12	0.13
L	12.68	12.9	13.2	0.49	0.51	0.52
L1	2.88	3.03	3.18	0.11	0.11	0.12
ØP3	3.15REF			0.124REF		
F3	3.15	3.30	3.45	0.12	0.13	0.13
G3	1.25	1.35	1.55	0.04	0.05	0.06
b1	1.18	1.28	1.43	0.04	0.05	0.05
b2	0.70	0.80	0.95	0.02	0.03	0.03

TO-220MF Part Marking Information

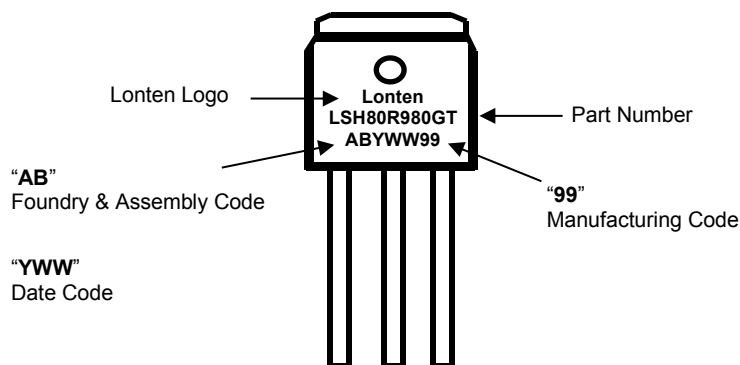


Mechanical Dimensions for TO-251

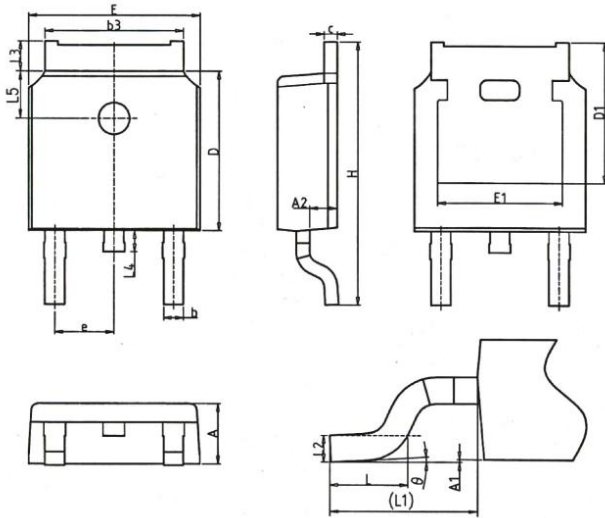


COMMON DIMENSIONS			
SYMBOL	MM		
	MIN	NOM	MAX
A	2.20	2.30	2.38
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b2	0.00	0.04	0.10
b2'	0.00	0.04	0.10
b3	5.20	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.73
E1	4.63	—	—
e	2.286BSC		
H	16.22	16.52	16.82
L1	9.15	9.40	9.65
L3	0.88	1.02	1.28
L5	1.65	1.80	1.95

TO-251 Part Marking Information

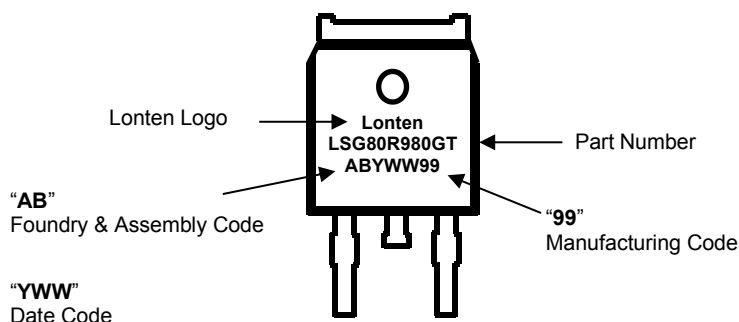


Mechanical Dimensions for TO-252

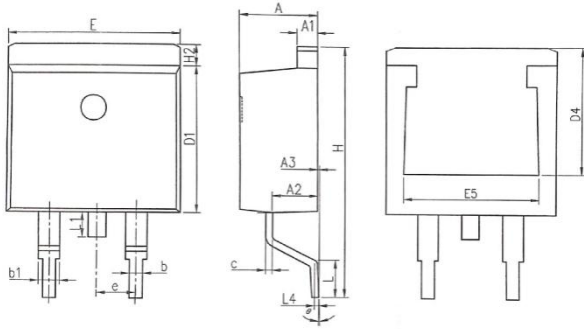


COMMON DIMENSIONS			
SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.38
A1	0.00	—	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.73
E1	4.63	—	—
e	2.286BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90REF		
L2	0.51BSC		
L3	0.88	—	1.28
L4	0.50	—	1.00
L5	1.65	1.80	1.95
θ	0°	—	8°

TO-252 Part Marking Information

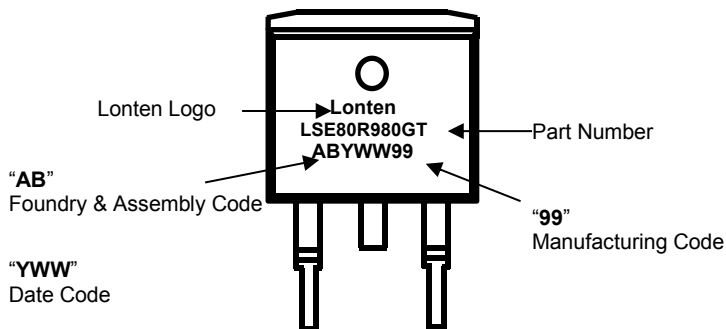


Mechanical Dimensions for TO-263



COMMON DIMENSIONS						
SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.37	4.57	4.77	0.172	0.180	0.188
A1	1.22	1.27	1.42	0.048	0.050	0.056
A2	2.49	2.89	2.89	0.098	0.114	0.114
A3	0.00	0.13	0.25	0.000	0.005	0.010
b	0.70	0.81	0.96	0.028	0.032	0.034
b1	1.17	1.27	1.47	0.046	0.050	0.058
c	0.30	0.38	0.53	0.012	0.015	0.021
D1	8.50	8.70	8.90	0.335	0.343	0.350
D4	6.60	—	—	0.260	—	—
E	9.86	10.16	10.36	0.389	0.400	0.408
E5	7.06	—	—	0.278	—	—
e	2.54 BSC			0.100 BSC		
H	14.70	15.10	15.50	0.579	0.594	0.610
H2	1.07	1.27	1.47	0.042	0.050	0.058
L	2.00	2.30	2.60	0.079	0.091	0.102
L1	1.40	1.55	1.70	0.055	0.061	0.067
L4	0.25 BSC			0.010 BSC		
θ	0°	5°	9°	0°	0.197°	0.354°

TO-263 Part Marking Information



Disclaimer

The content specified herein is for the purpose of introducing LONTEN's products (hereinafter "Products"). The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. Examples of application circuits, circuit constants and any other information contained herein illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.

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